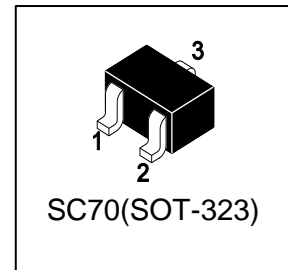


LBC847CWT1G

S-LBC847CWT1G

General Purpose Transistors NPN Silicon

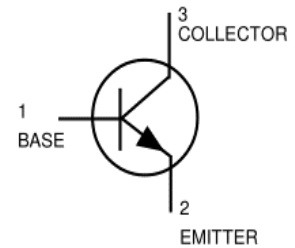


1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBC847CWT1G	1G	3000/Tape&Reel



3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	45	V
Collector–Base Voltage	VCBO	50	V
Emitter–Base Voltage	VEBO	6	V
Collector Current — Continuous	IC	100	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation,	PD	150	mW
Thermal Resistance, Junction–to–Ambient	ROJA	833	°C/W
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 10 mA, IB = 0)	VBR(CEO)	45	-	-	V
Collector–Emitter Breakdown Voltage (IC = 10 μA, VEB = 0)	VBR(CES)	50	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μA, IE= 0)	VBR(CBO)	50	-	-	V
Emitter–Base Breakdown Voltage (IE = 1.0 μA, IC = 0)	VBR(EBO)	6	-	-	V
Collector Cutoff Current (VCB = 30 V) (VCB = 30 V, TA = 150°C)	ICBO	-	-	15 5	nA μA
Collector-Emitter cutoff Current (VCE=45V, IB=0)	ICEO	-	-	10	μA

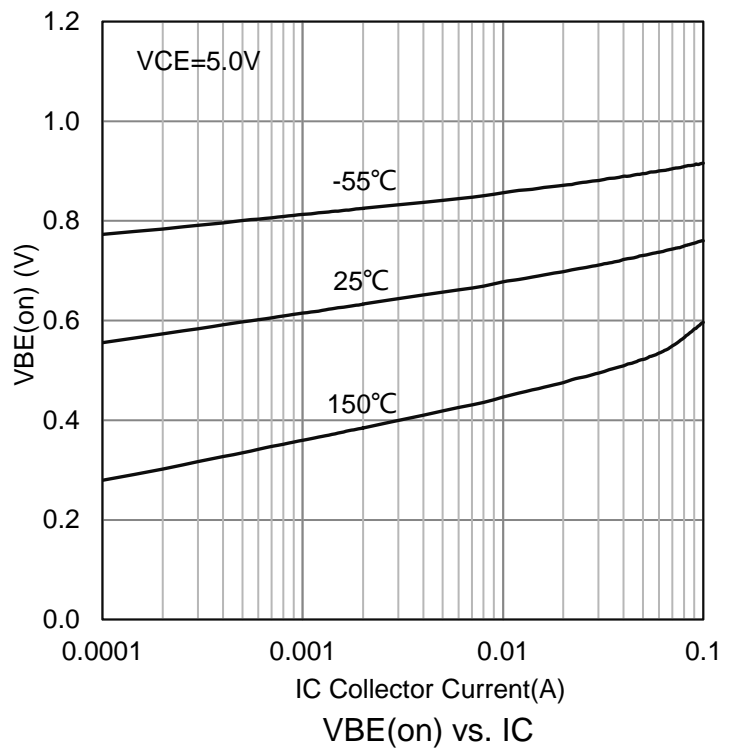
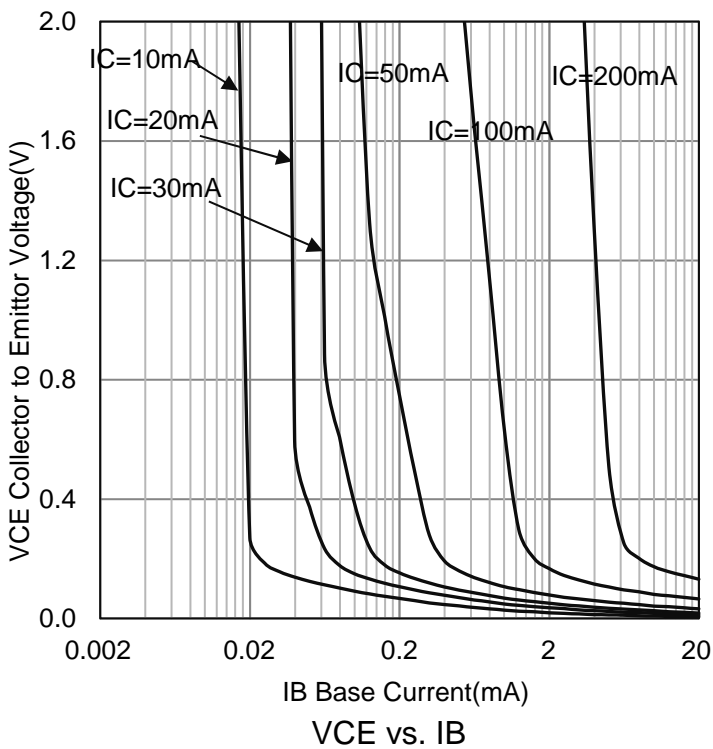
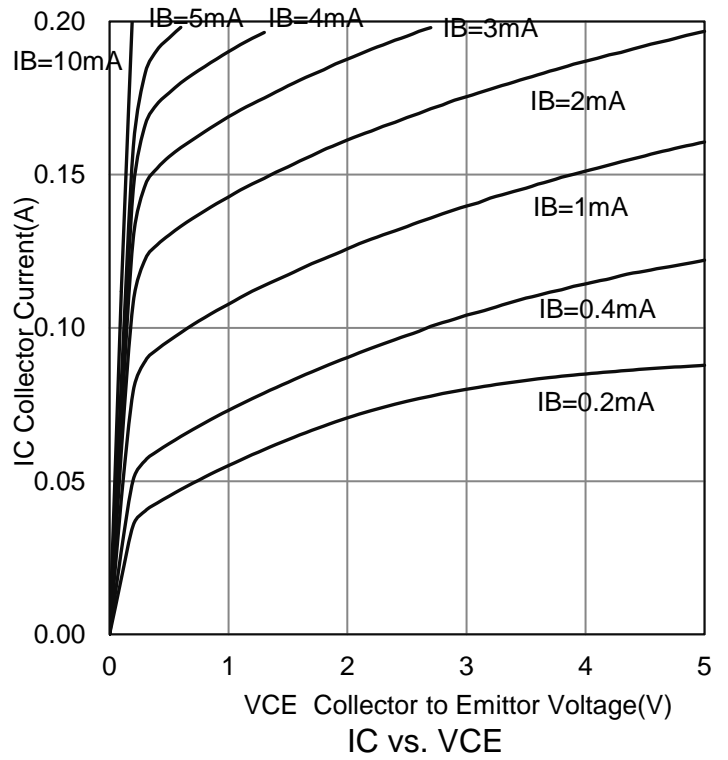
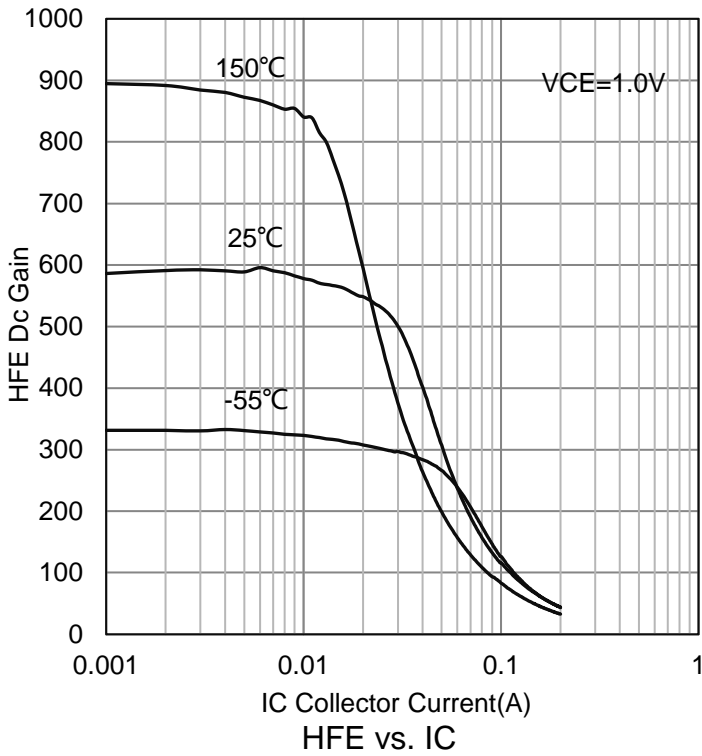
ON CHARACTERISTICS

DC Current Gain (IC = 2.0 mA, VCE = 5.0 V)	HFE	420	520	800	
Collector–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VCE(sat)	- -	- -	0.25 0.6	V
Base–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VBE(sat)	- -	0.7 0.9	0.9 1.2	V
Base–Emitter turn on Voltage (IC = 2.0 mA, VCE = 5.0 V) (IC = 10 mA, VCE = 5.0 V)	VBE(on)	580 -	660 -	700 770	mV

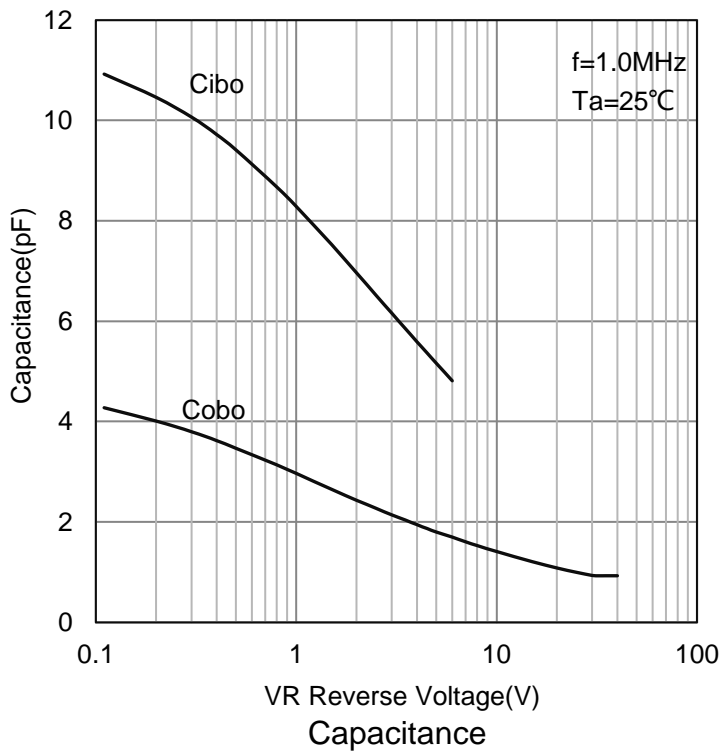
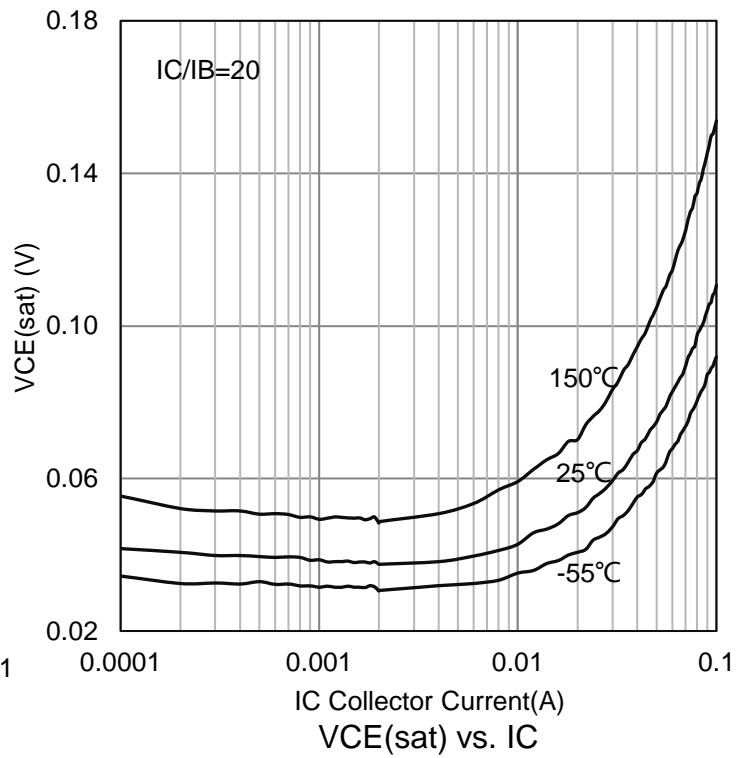
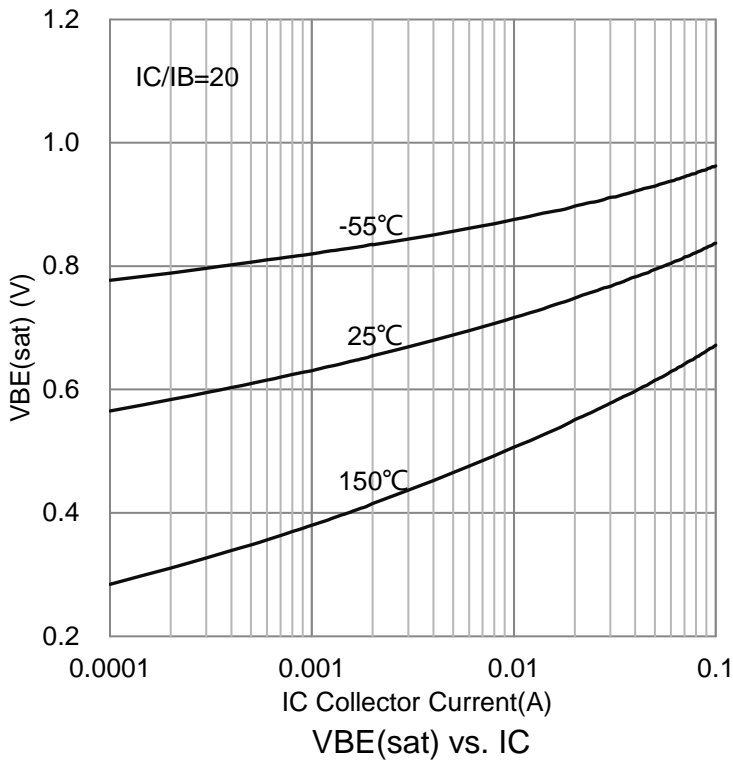
SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (IC = 10 mA, VCE = 5.0 V, f = 100 MHz)	fT	100	-	-	MHz
Output Capacitance (VCB = 10 V, f = 1.0 MHz)	Cobo	-	-	4.5	pF
Noise Figure (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 kΩ f = 1.0 kHz, BW = 200 Hz)	NF	-	-	4	dB

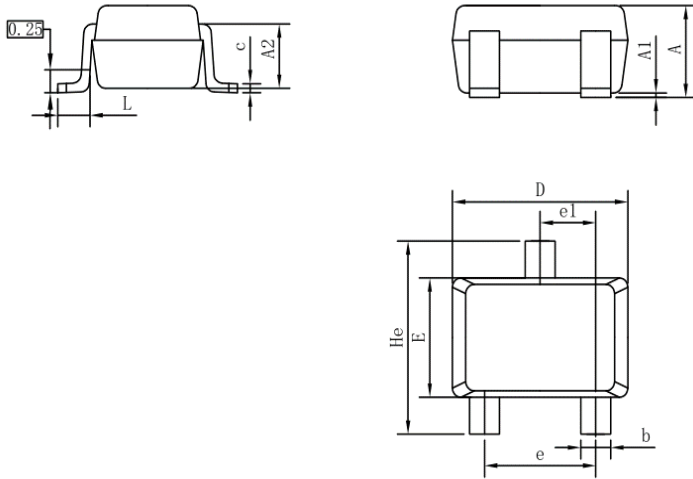
6.ELECTRICAL CHARACTERISTICS CURVES



6.ELECTRICAL CHARACTERISTICS CURVES(Con.)

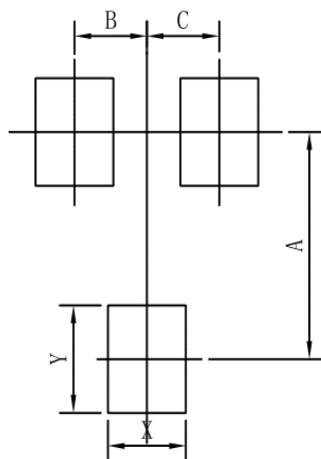


7.OUTLINE AND DIMENSIONS



SC70			
DIM	MIN	NOR	MAX
A	0.80	0.95	1.00
A1	0.00	0.05	0.10
A2	0.7 REF		
b	0.30	0.35	0.40
c	0.10	0.15	0.25
D	1.80	2.05	2.20
E	1.15	1.30	1.35
e	1.20	1.30	1.40
e1	0.65 BSC		
L	0.20	0.35	0.56
He	2.00	2.10	2.40
ALL Dimension in mm			

8.SOLDERING FOOTPRINT



SC70	
DIM	MIN
A	1.90
B	0.65
C	0.65
X	0.70
Y	0.90

DISCLAIMER

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- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

单击下面可查看定价，库存，交付和生命周期等信息

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